

MOSFET – N-Channel, SUPREMOS

600 V, 76 A, 36 mΩ

FCH76N60N

Description

The SUPREMOS[®] MOSFET is ON Semiconductor's next generation of high voltage super-junction (SJ) technology employing a deep trench filling process that differentiates it from the conventional SJ MOSFETs. This advanced technology and precise process control provides lowest R_{sp on}-resistance, superior switching performance and ruggedness. SUPREMOS MOSFET is suitable for high frequency switching power converter applications such as PFC, server/telecom power, FPD TV power, ATX power and industrial power applications.

Features

- R_{DS(on)} = 28 mΩ (Typ.) @ V_{GS} = 10 V, I_D = 38 A
- Ultra Low Gate Charge (Typ. Q_g = 218 nC)
- Low Effective Output Capacitance (Typ. C_{oss(eff.)} = 914 pF)
- 100% Avalanche Tested
- This Device is Pb-Free and is RoHS Compliant

Applications

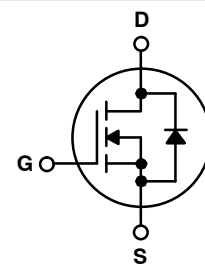
- Solar Inverter
- AC-DC Power Supply



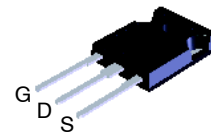
ON Semiconductor[®]

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V _{DS}	R _{DS(ON)} MAX	I _D MAX
600 V	36 mΩ @ 10 V	76 A

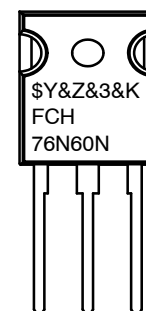


N-CHANNEL MOSFET



TO-247-3LD
CASE 340CK

MARKING DIAGRAM



\$Y	= ON Semiconductor Logo
&Z	= Assembly Plant Code
&3	= Numeric Date Code
&K	= Lot Code
FCH76N60N	= Specific Device Code

ORDERING INFORMATION

See detailed ordering and shipping information on page 2 of this data sheet.

FCH76N60N

MOSFET MAXIMUM RATINGS ($T_C = 25^\circ\text{C}$ unless otherwise noted)

Symbol	Parameter	FCH76N60N	Unit
V_{DSS}	Drain to Source Voltage	600	V
V_{GSS}	Gate to Source Voltage	± 30	V
I_D	Drain Current	- Continuous ($T_C = 25^\circ\text{C}$)	76
		- Continuous ($T_C = 100^\circ\text{C}$)	48.1
I_{DM}	Drain Current	- Pulsed (Note 1)	228
E_{AS}	Single Pulsed Avalanche Energy (Note 2)	8022	mJ
I_{AR}	Avalanche Current (Note 1)	25.3	A
E_{AR}	Repetitive Avalanche Energy (Note 1)	5.43	mJ
dv/dt	MOSFET dv/dt	100	V/ns
	Peak Diode Recovery dv/dt (Note 3)	20	
P_D	Power Dissipation	($T_C = 25^\circ\text{C}$)	543
		- Derate above 25°C	4.34
T_J, T_{STG}	Operating and Storage Temperature Range	-55 to + 150	$^\circ\text{C}$
T_L	Maximum Lead Temperature for Soldering, 1/8" from Case for 5 Second	300	$^\circ\text{C}$

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

1. Repetitive Rating: pulse-width limited by maximum junction temperature.

2. $I_{AS} = 25.3$ A, $R_G = 25 \Omega$, starting $T_J = 25^\circ\text{C}$

3. $I_{SD} \leq 76$ A, $di/dt \leq 200$ A/ μs , $V_{DD} \leq 380$ V, starting $T_J = 25^\circ\text{C}$

THERMAL CHARACTERISTICS

Symbol	Parameter	FCH76N60N	Unit
$R_{\theta JC}$	Thermal Resistance, Junction to Case, Max.	0.23	$^\circ\text{C}/\text{W}$
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient, Max.	40	

PACKAGE MARKING AND ORDERING INFORMATION

Part Number	Top Mark	Package	Package Method	Reel Size	Tape Width	Quantity
FCH76N60N	FCH76N60N	TO-247-3LD	Tube	N/A	N/A	30 Units

FCH76N60N

ELECTRICAL CHARACTERISTICS (T_C = 25°C unless otherwise noted)

Symbol	Parameter	Test Condition	Min.	Typ.	Max.	Unit
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OFF CHARACTERISTICS

BV _{DSS}	Drain to Source Breakdown Voltage	I _D = 250 μA, V _{GS} = 0 V, T _C = 25°C	600	–	–	V
ΔBV _{DSS} / ΔT _J	Breakdown Voltage Temperature Coefficient	I _D = 250 μA, Referenced to 25°C	–	0.73	–	V/°C
I _{DSS}	Zero Gate Voltage Drain Current	V _{DS} = 480 V, V _{GS} = 0 V	–	–	10	μA
		V _{DS} = 480 V, V _{GS} = 0 V, T _C = 125°C	–	–	100	
I _{GSS}	Gate to Body Leakage Current	V _{GS} = ±30 V, V _{DS} = 0 V	–	–	±100	nA

ON CHARACTERISTICS

V _{GS(th)}	Gate Threshold Voltage	V _{GS} = V _{DS} , I _D = 250 μA	2.0	–	4.0	V
R _{DS(on)}	Static Drain to Source On Resistance	V _{GS} = 10 V, I _D = 38 A	–	28	36	mΩ
g _{FS}	Forward Transconductance	V _{DS} = 20 V, I _D = 38 A	–	90	–	S

DYNAMIC CHARACTERISTICS

C _{iss}	Input Capacitance	V _{DS} = 100 V, V _{GS} = 0 V, f = 1 MHz	–	9310	12385	pF
C _{oss}	Output Capacitance		–	370	495	pF
C _{rss}	Reverse Transfer Capacitance		–	3.1	5	pF
C _{oss}	Output Capacitance	V _{DS} = 380 V, V _{GS} = 0 V, f = 1 MHz	–	195	–	pF
C _{oss(eff.)}	Effective Output Capacitance	V _{DS} = 0 V to 380 V, V _{GS} = 0 V	–	914	–	pF
Q _{g(tot)}	Total Gate Charge at 10 V	V _{DS} = 380 V, I _D = 38 A, V _{GS} = 10 V (Note 4)	–	218	285	nC
Q _{gs}	Gate to Source Gate Charge		–	39	–	nC
Q _{gd}	Gate to Drain “Miller” Charge		–	66	–	nC
ESR	Equivalent Series Resistance (G–S)	f = 1 MHz	–	1.0	–	Ω

SWITCHING CHARACTERISTICS

t _{d(on)}	Turn-On Delay Time	V _{DD} = 380 V, I _D = 38 A, R _G = 25 Ω (Note 4)	–	34	78	ns
t _r	Turn-On Rise Time		–	24	58	ns
t _{d(off)}	Turn-Off Delay Time		–	235	480	ns
t _f	Turn-Off Fall Time		–	32	74	ns

DRAIN-SOURCE DIODE CHARACTERISTICS

I _S	Maximum Continuous Drain to Source Diode Forward Current	–	–	76	A	
I _{SM}	Maximum Pulsed Drain to Source Diode Forward Current	–	–	228	A	
V _{SD}	Drain to Source Diode Forward Voltage	V _{GS} = 0 V, I _{SD} = 38 A	–	–	1.2	V
t _{rr}	Reverse Recovery Time	V _{GS} = 0 V, I _{SD} = 38 A, dI _F /dt = 100 A/μs	–	612	–	ns
Q _{rr}	Reverse Recovery Charge		–	16	–	μC

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

4. Essentially Independent of Operating Temperature Typical Characteristics.

FCH76N60N

TYPICAL CHARACTERISTICS

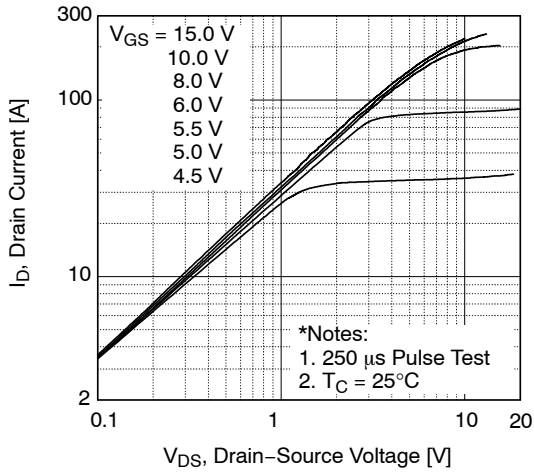


Figure 1. On-Region Characteristics

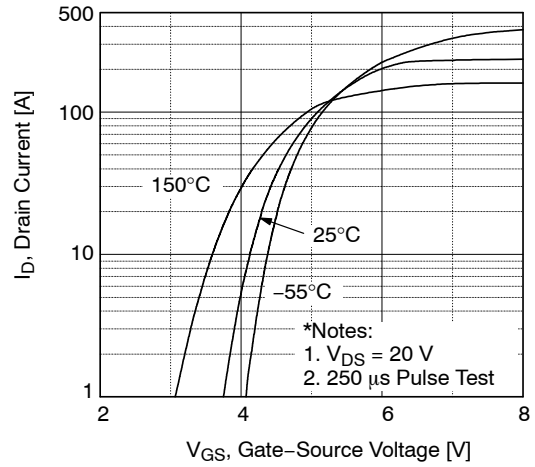


Figure 2. Transfer Characteristics

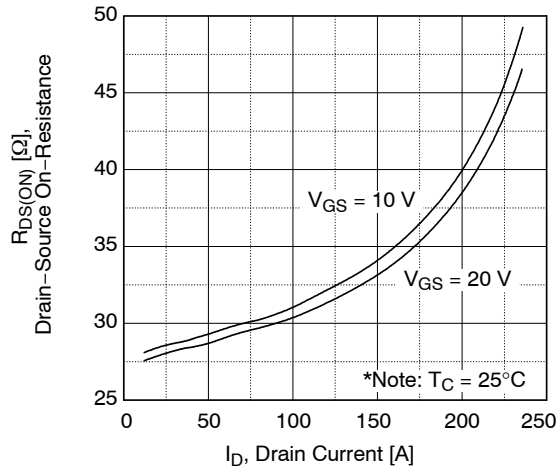


Figure 3. On-Resistance Variation vs. Drain Current and Gate Voltage

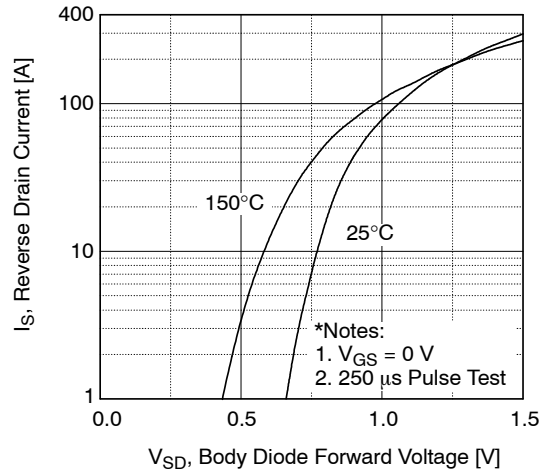


Figure 4. Body Diode Forward Voltage Variation vs. Source Current and Temperature

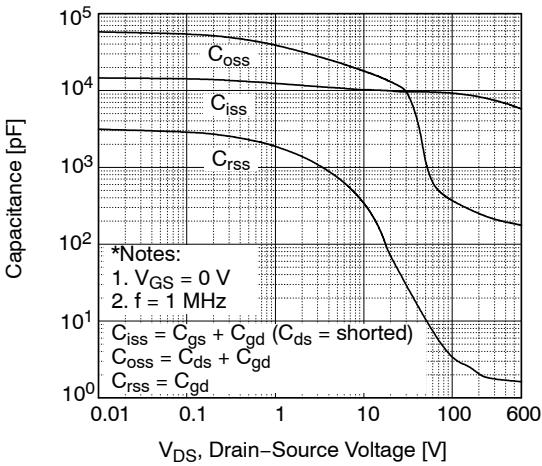


Figure 5. Capacitance Characteristics

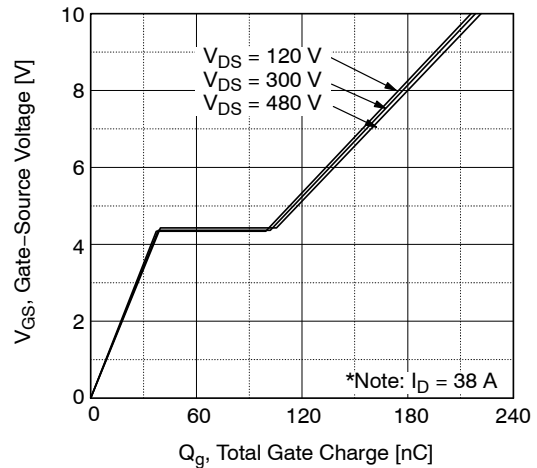


Figure 6. Gate Charge Characteristics

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TYPICAL CHARACTERISTICS (continued)

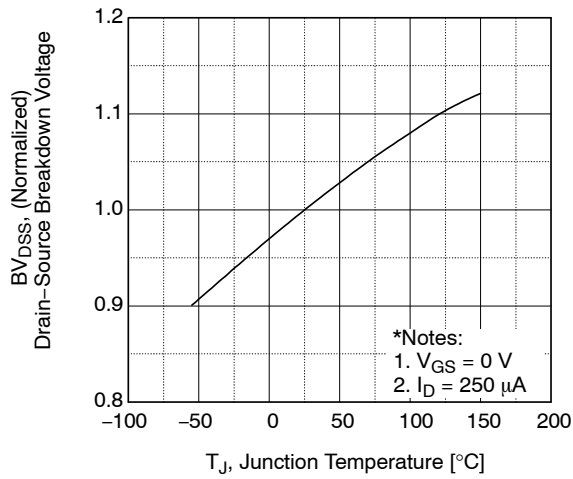


Figure 7. Breakdown Voltage Variation vs. Temperature

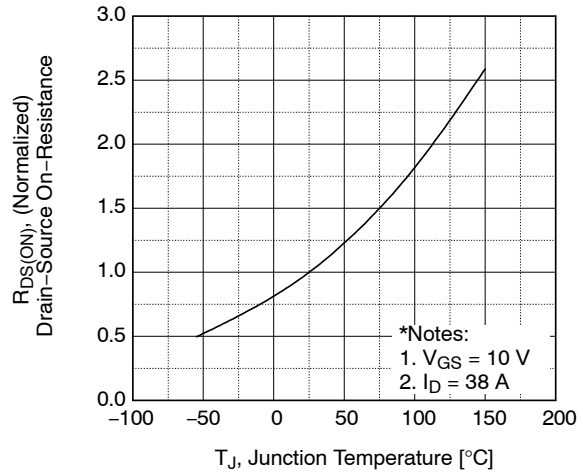


Figure 8. On-Resistance Variation vs. Temperature

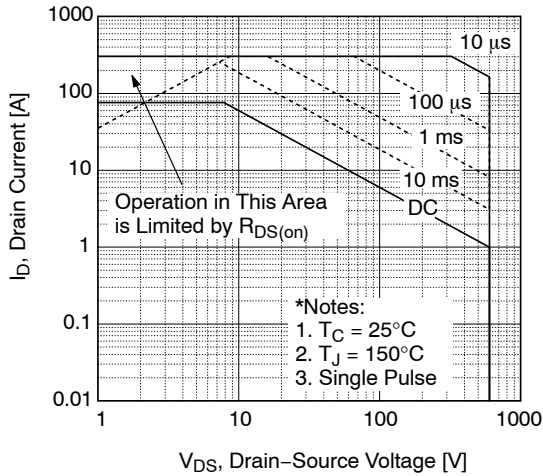


Figure 9. Maximum Safe Operating Area

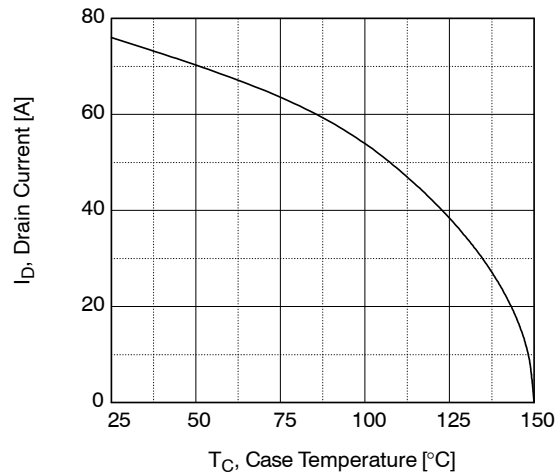


Figure 10. Maximum Drain Current vs. Case Temperature

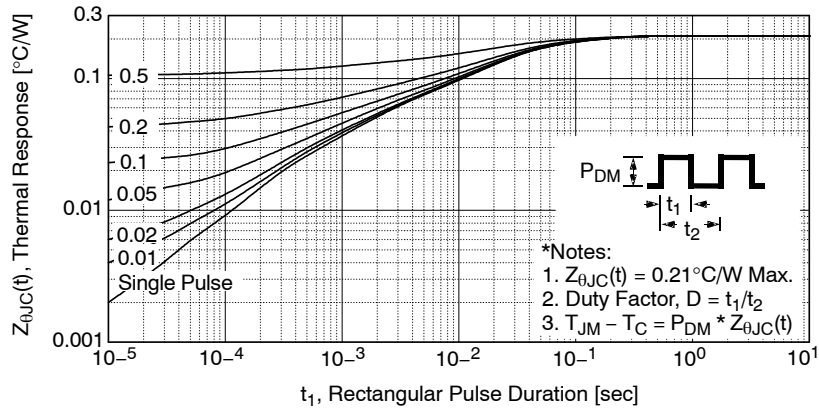


Figure 11. Transient Thermal Response Curve

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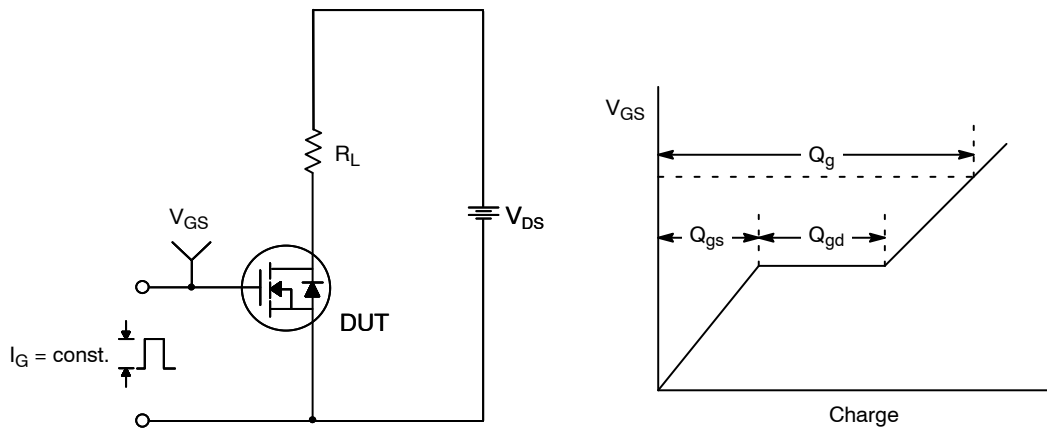


Figure 12. Gate Charge Test Circuit & Waveform

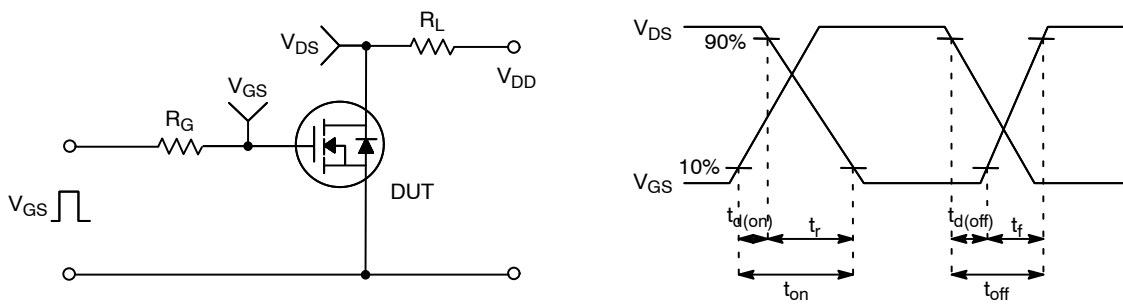


Figure 13. Resistive Switching Test Circuit & Waveforms

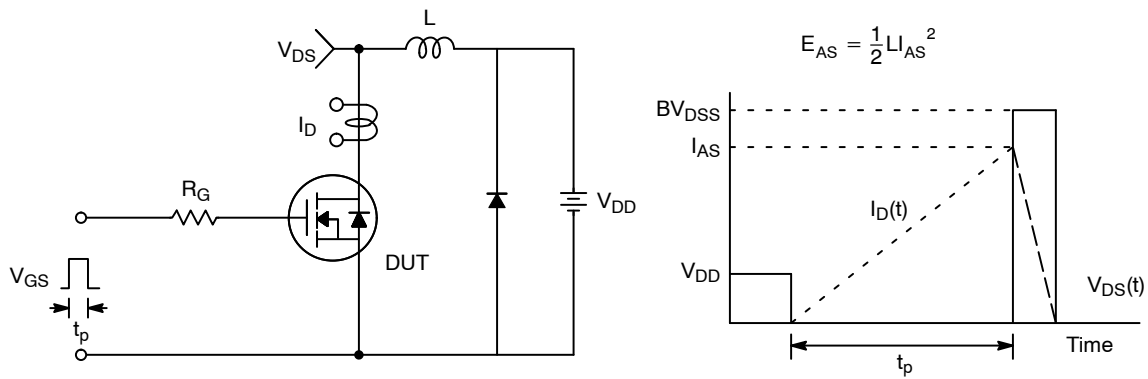


Figure 14. Unclamped Inductive Switching Test Circuit & Waveforms

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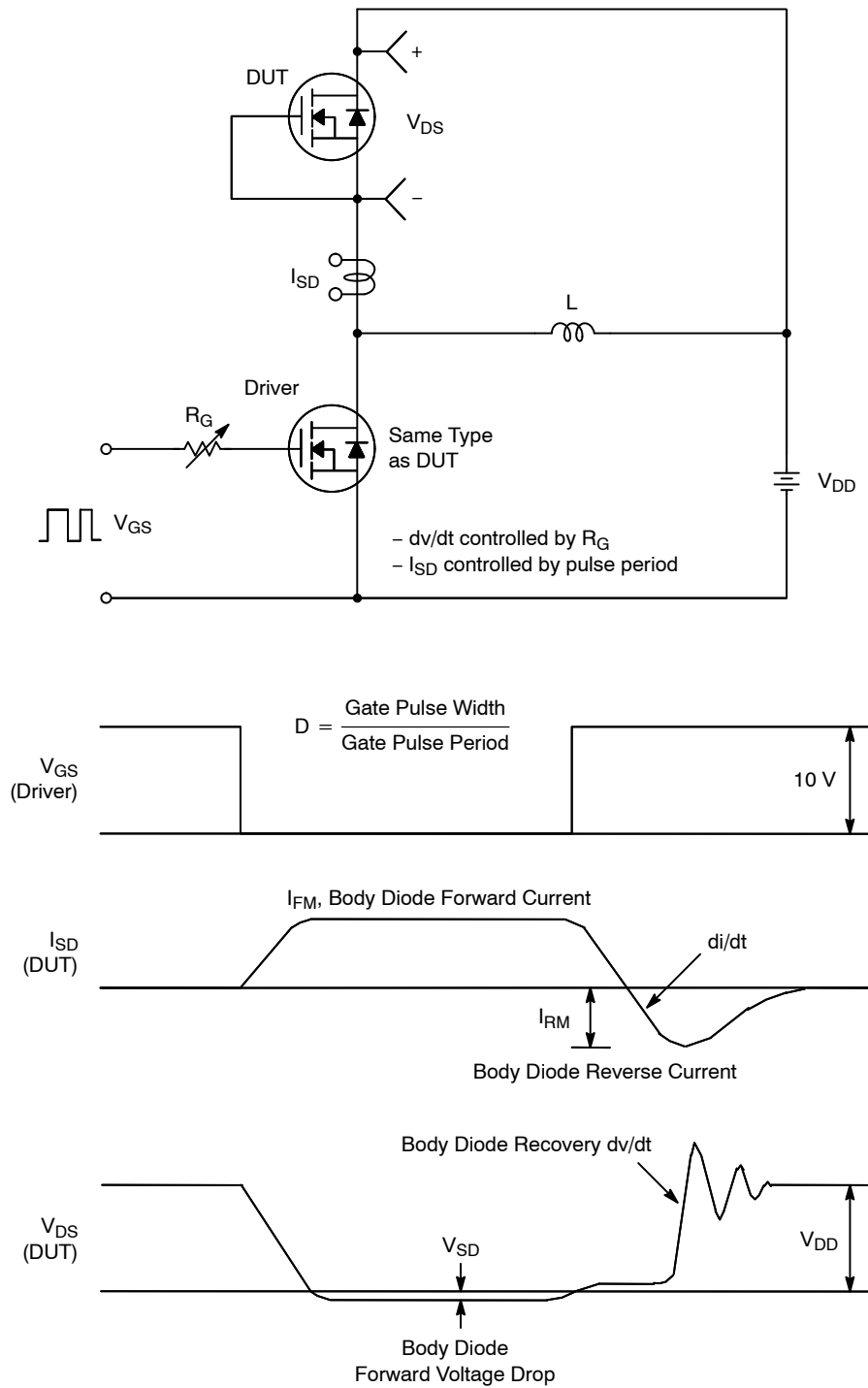
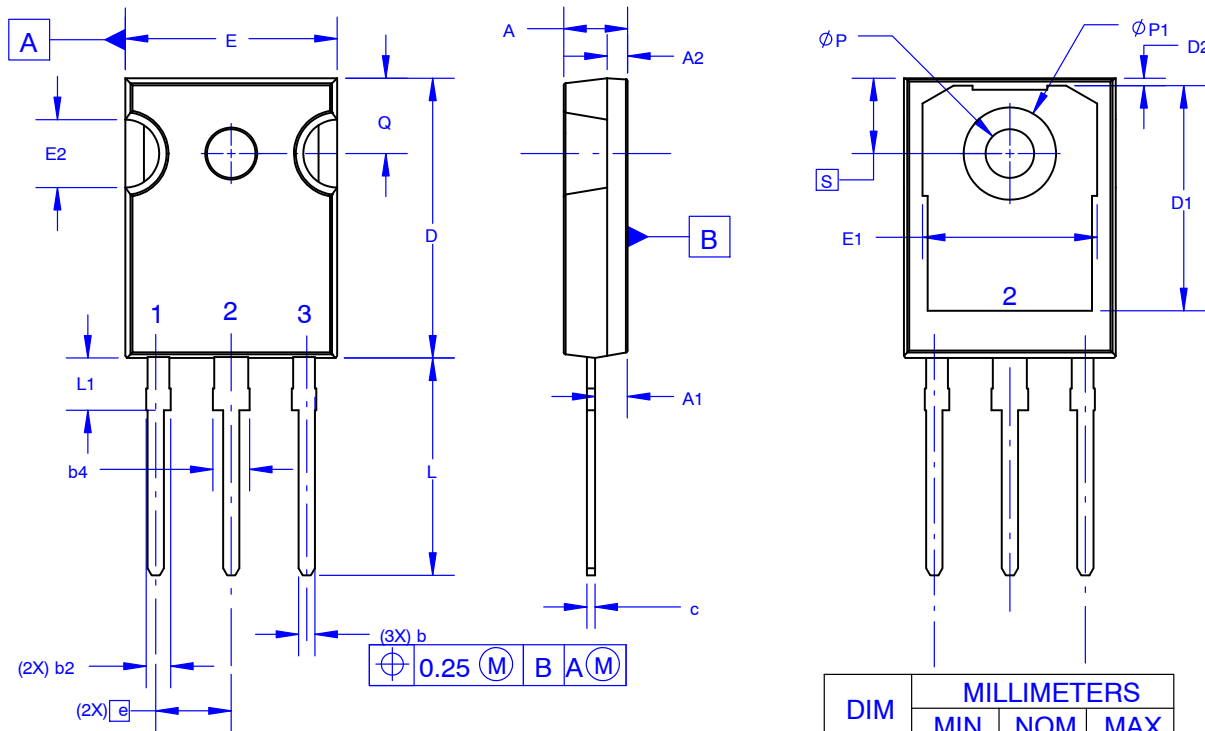


Figure 15. Peak Diode Recovery dv/dt Test Circuit & Waveforms

TO-247-3LD SHORT LEAD
CASE 340CK
ISSUE A

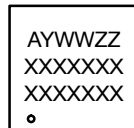
DATE 31 JAN 2019



NOTES: UNLESS OTHERWISE SPECIFIED.

- A. DIMENSIONS ARE EXCLUSIVE OF BURRS, MOLD FLASH, AND TIE BAR EXTRUSIONS.
- B. ALL DIMENSIONS ARE IN MILLIMETERS.
- C. DRAWING CONFORMS TO ASME Y14.5 - 2009.
- D. DIMENSION A1 TO BE MEASURED IN THE REGION DEFINED BY L1.
- E. LEAD FINISH IS UNCONTROLLED IN THE REGION DEFINED BY L1.

GENERIC MARKING DIAGRAM*



- XXXX = Specific Device Code
- A = Assembly Location
- Y = Year
- WW = Work Week
- ZZ = Assembly Lot Code

*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "•", may or may not be present. Some products may not follow the Generic Marking.

DIM	MILLIMETERS		
	MIN	NOM	MAX
A	4.58	4.70	4.82
A1	2.20	2.40	2.60
A2	1.40	1.50	1.60
b	1.17	1.26	1.35
b2	1.53	1.65	1.77
b4	2.42	2.54	2.66
c	0.51	0.61	0.71
D	20.32	20.57	20.82
D1	13.08	~	~
D2	0.51	0.93	1.35
E	15.37	15.62	15.87
E1	12.81	~	~
E2	4.96	5.08	5.20
e	~	5.56	~
L	15.75	16.00	16.25
L1	3.69	3.81	3.93
∅P	3.51	3.58	3.65
∅P1	6.60	6.80	7.00
Q	5.34	5.46	5.58
S	5.34	5.46	5.58

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